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November 2013

FQP13N10

N-Channel QFET $^{\circledR}$ MOSFET 100 V, 12.8 A, 180 m $_{\Omega}$

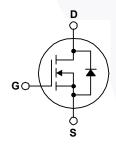
Description

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor control, and variable switching power applications.

Features

- 12.8 A, 100 V, $R_{DS(on)}$ = 180 m Ω (Max.) @ V_{GS} = 10 V, I_D = 6.4 A
- Low Gate Charge (Typ. 12 nC)
- · Low Crss (Typ. 20 pF)
- · 100% Avalanche Tested
- 175°C Maximum Junction Temperature Rating





Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol	Parameter		FQP13N10	Unit
V _{DSS}	Drain-Source Voltage		100	V
I _D	Drain Current - Continuous (T _C = 25°C)		12.8	А
	- Continuous (T _C = 100°C)		9.05	А
I _{DM}	Drain Current - Pulsed	(Note 1)	51.2	А
V _{GSS}	Gate-Source Voltage		± 25	V
E _{AS}	Single Pulsed Avalanche Energy	(Note 2)	95	mJ
I _{AR}	Avalanche Current	(Note 1)	12.8	А
E _{AR}	Repetitive Avalanche Energy	(Note 1)	6.5	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)		6.0	V/ns
P_{D}	Power Dissipation (T _C = 25°C)		65	W
	- Derate above 25°C		0.43	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +175	°C
TL	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 seconds		300	°C
'L			300	C

Thermal Characteristics

Symbol	Parameter	FQP13N10	Unit	
$R_{ heta JC}$	Thermal Resistance, Junction-to-Case, Max.	2.31	°C/W	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	°C/W	

Marking and Ordering Information

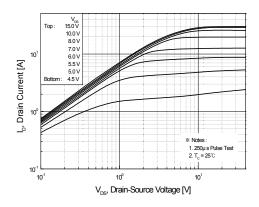
Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQP13N10	FQP13N10	TO-220	Tube	N/A	N/A	50 units

Electrical Characteristics To = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Тур	Max	Unit
Off Cha	aracteristics					
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0 V, I _D = 250 μA	100			V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 250 μA, Referenced to 25°0		0.09		V/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 100 V, V _{GS} = 0 V			1	μΑ
	ero Gale vollage Drain Current	V _{DS} = 80 V, T _C = 150°C			10	μΑ
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 25 V, V _{DS} = 0 V			100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -25 V, V _{DS} = 0 V			-100	nA
On Cha	aracteristics					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	2.0		4.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10 V, I _D = 6.4 A		0.142	0.18	Ω
9 _{FS}	Forward Transconductance	V _{DS} = 40 V, I _D = 6.4 A		6.8		S
C _{iss}	Input Capacitance Output Capacitance	V _{DS} = 25 V, V _{GS} = 0 V, f = 1.0 MHz		345 100	450 130	pF pF
	ic Characteristics			245	450	
C _{rss}	Reverse Transfer Capacitance	t = 1.0 MHz		20	25	pF
orss	Treverse Transier Oapacitance			20	20	Pi
Switch	ing Characteristics					
t _{d(on)}	Turn-On Delay Time	V _{DD} = 50 V, I _D = 12.8 A,		5	20	ns
t _r	Turn-On Rise Time	$R_G = 25 \Omega$		55	120	ns
t _{d(off)}	Turn-Off Delay Time	NG 20 32		20	50	ns
t _f	Turn-Off Fall Time	(Note	4)	25	60	ns
Qg	Total Gate Charge	V _{DS} = 80 V, I _D = 12.8 A,		12	16	nC
Q _{gs}	Gate-Source Charge	V _{GS} = 10 V	A	2.5		nC
Q _{gd}	Gate-Drain Charge	(Note 4		5.1		nC
\			·			
	Source Diode Characteristics and Max				40.0	
l _S	Maximum Continuous Drain-Source Diode Forward Current				12.8	A
ISM	Maximum Pulsed Drain-Source Diode Forward				51.2	A
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 12.8 A			1.5	V
t _{rr}	Reverse Recovery Time	$V_{GS} = 0 \text{ V, } I_{S} = 12.8 \text{ A,}$ $dI_{F} / dt = 100 \text{ A/}\mu\text{s}$		72		ns
Q _{rr}	Reverse Recovery Charge	$dI_F / dt = 100 A/\mu s$		0.17	-	μC

- **Notes:** 1. Repetitive Rating : Pulse width limited by maximum junction temperature. 2. L = 0.87 mH, I_{AS} = 12.8 A, V_{DD} = 25 V, R_G = 25 Ω , starting T_J = 25°C. 3. $I_{SD} \le 12.8$ A, di/dt ≤ 300 A/µs, $V_{DD} \le BV_{DSS}$ starting T_J = 25°C. 4. Essentially Independent of Operating Temperature.

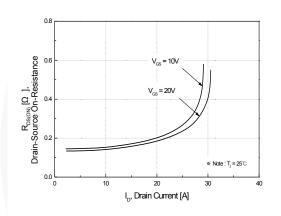
Typical Characteristics



V_{GS}, Gate-Source Voltage [V]

Figure 1. On-Region Characteristics

Figure 2. Transfer Characteristics



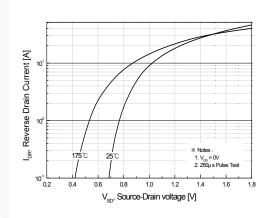
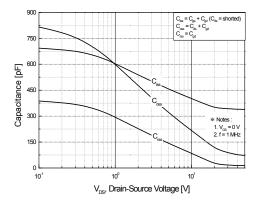


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature



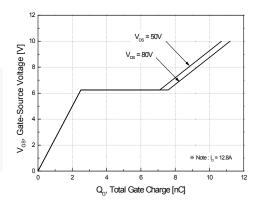


Figure 5. Capacitance Characteristics

Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

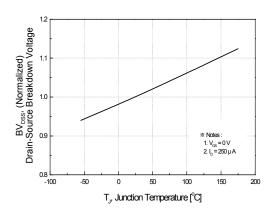
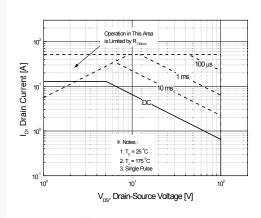


Figure 7. Breakdown Voltage Variation vs. Temperature

Figure 8. On-Resistance Variation vs. Temperature



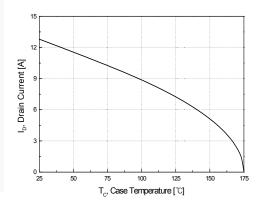


Figure 9. Maximum Safe Operating Area

Figure 10. Maximum Drain Current vs. Case Temperature

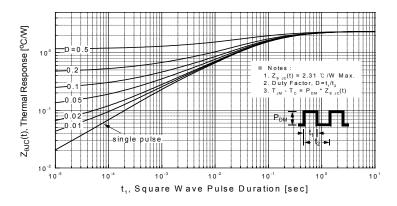


Figure 11. Transient Thermal Response Curve

Figure 12. Gate Charge Test Circuit & Waveform

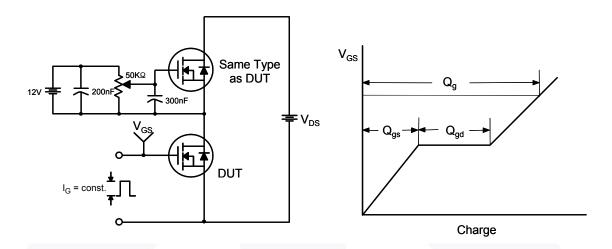


Figure 13. Resistive Switching Test Circuit & Waveforms

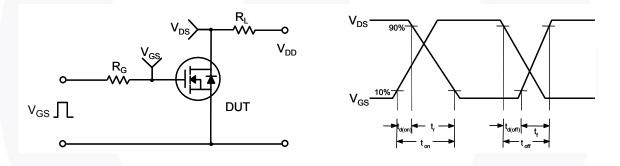
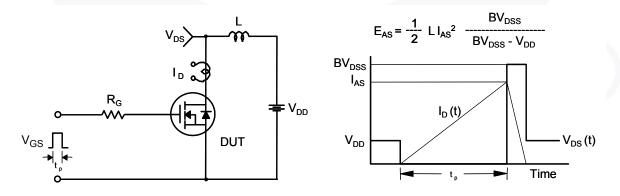


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



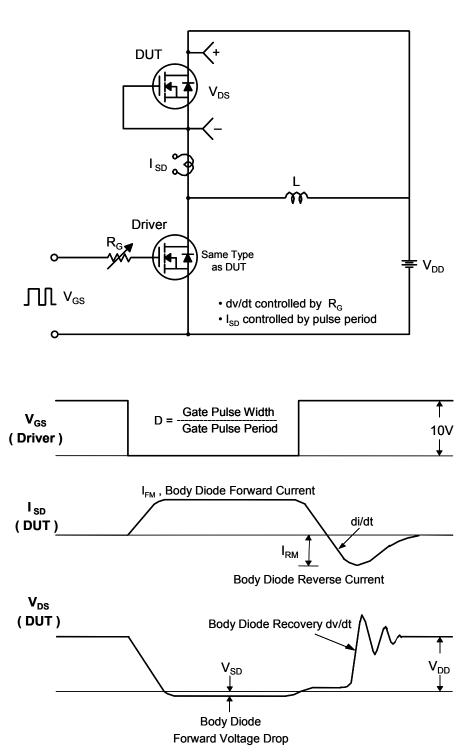
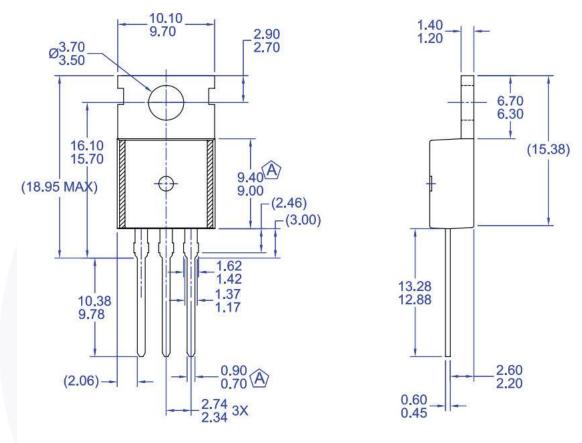
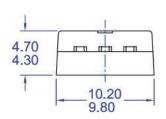


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

Mechanical Dimensions





NOTES:

- (A) CONFORMS TO JEDEC TO-220 VARIATION AB EXCEPT WHERE NOTED
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.
- D) DRAWING FILE/REVISION: MKT-TO220Y03REV1

Figure 16. TO220, Molded, 3-Lead, Jedec Variation AB

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